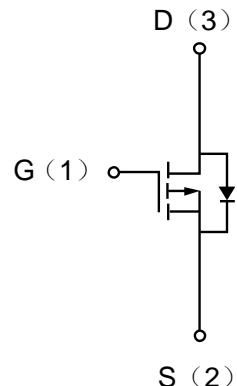


Description

The enhancement mode MOS is extremely high density cell and low on-resistance.

MOSFET Product Summary		
V _{DS} (V)	R _{D(on)} (Ω)	I _D (A)
-20	0.08 @ V _{GS} =-4.5V	-2.8
	0.11 @ V _{GS} =-2.5V	

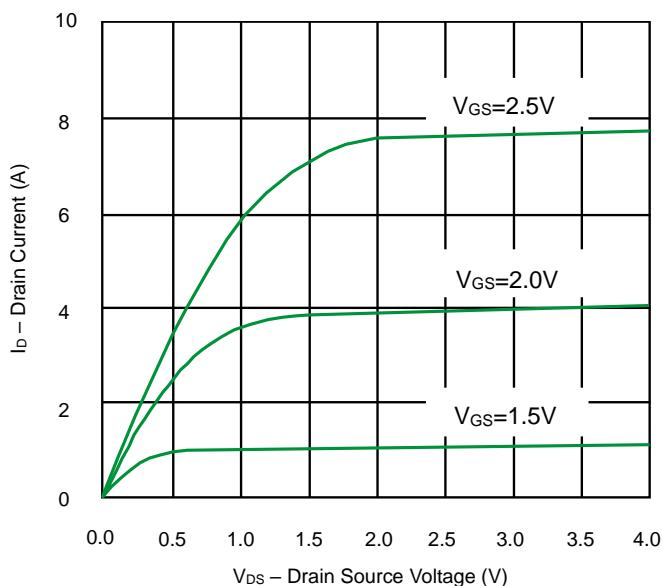
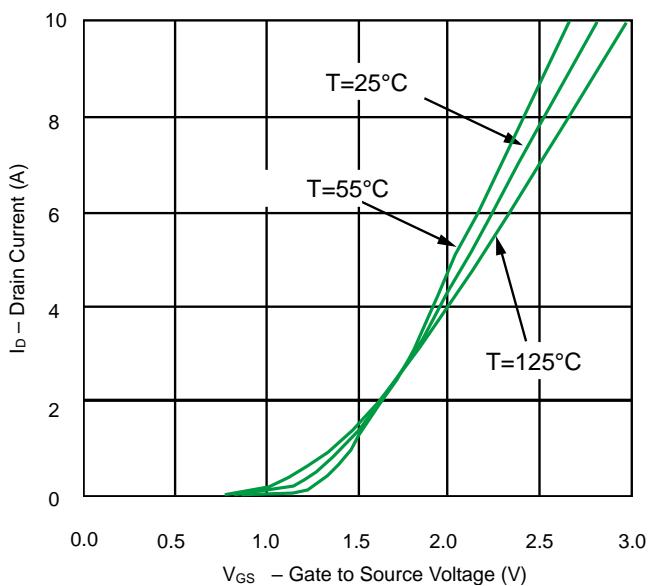
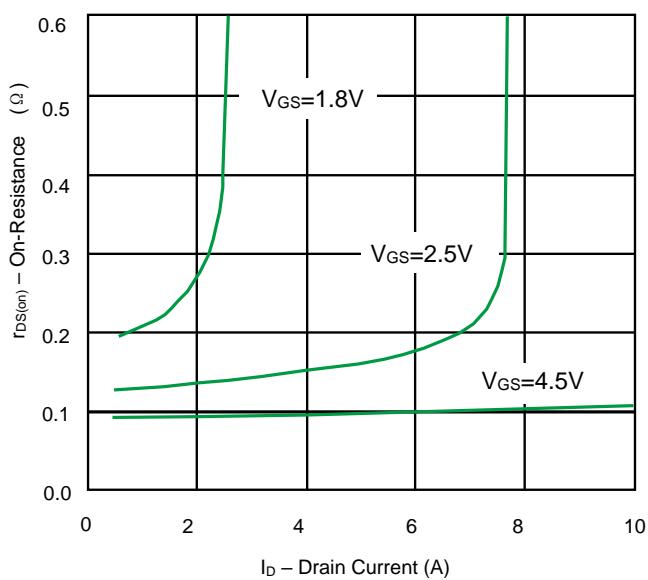
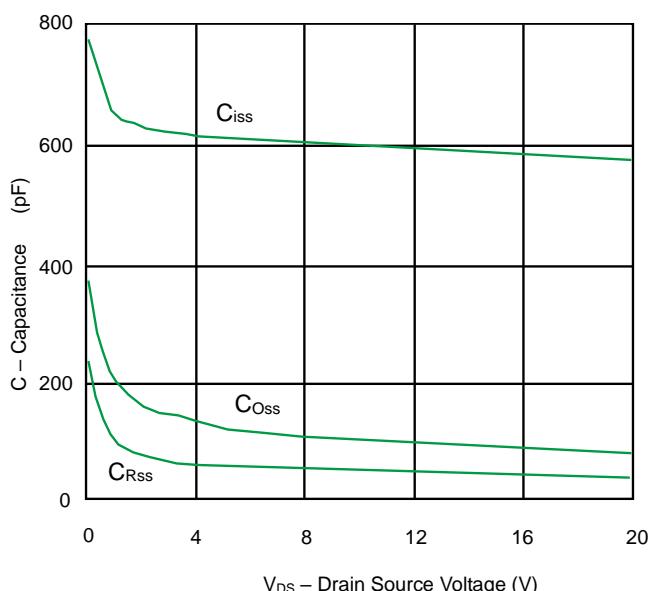


Electrical characteristics per line@25°C(unless otherwise specified)

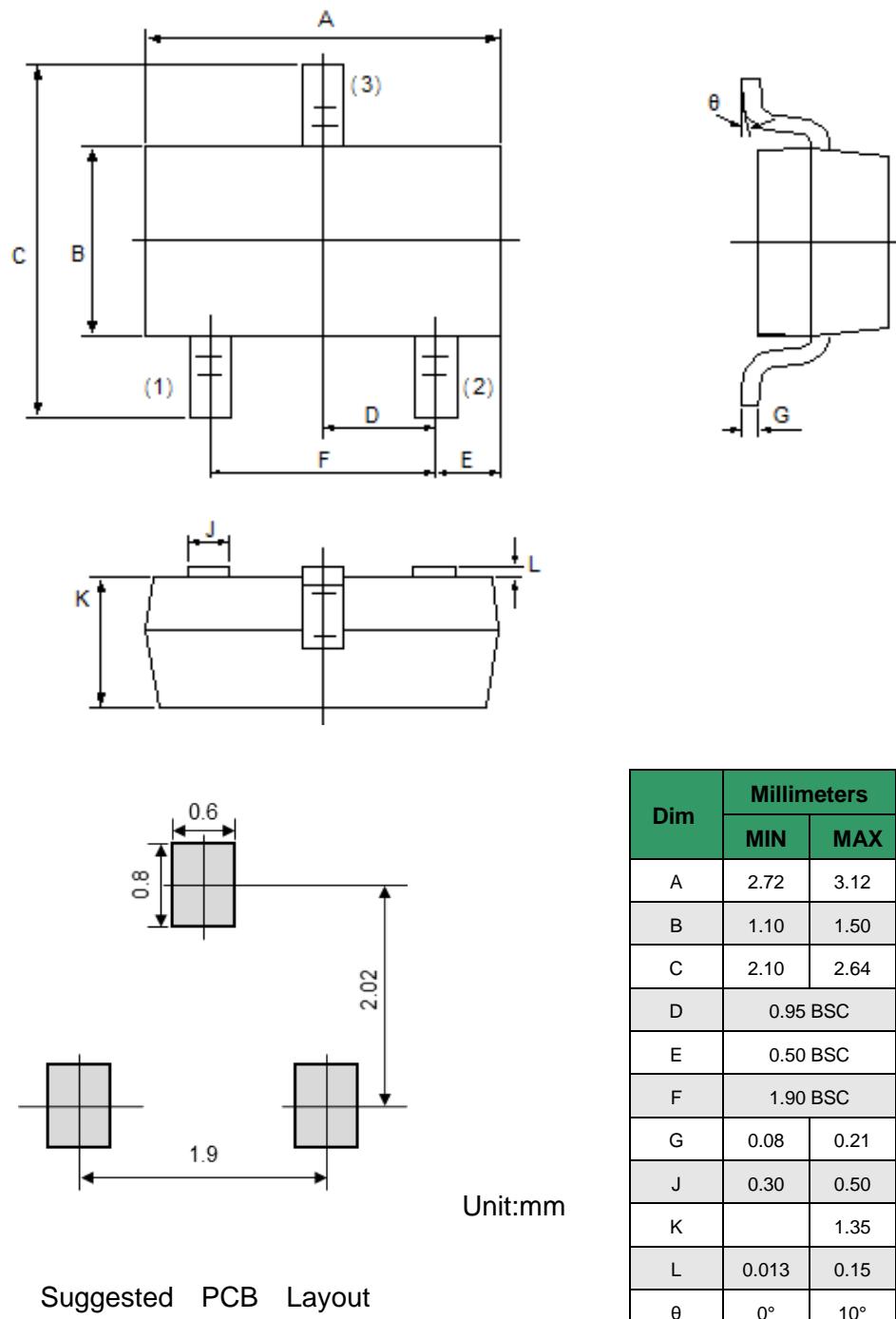
Parameter	Symbol	Conditions	Min.	Typ.	Max.	Units
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = -250μA, V _{GS} = 0V	-20	-	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -20V, V _{GS} = 0V	-	-	-1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} = 0V, V _{GS} = ±8V	-	-	±100	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250μA	-0.45		-0.9	V
Static Drain-Source On-Resistance	R _{D(on)}	V _{GS} = -4.5V, I _D = -2.8A	-	0.08	0.11	Ω
		V _{GS} = -2.5V, I _D = -2.0A	-	0.11	0.15	Ω
Forward Transistor conductance	g _{FS}	V _{GS} = 5V, I _D = 50mA, T _A = 125°C		6.5		S
DYNAMIC PARAMETERS						
Input Capacitance	C _{ISS}	V _{GS} = 0V, V _{DS} = 10V, f = 1MHz	-	360		pF
Output Capacitance	C _{DSS}		-	125		pF
Reverse Transfer Capacitance	C _{RSS}		-	50		pF
SWITCHING PARAMETERS						
Turn-On Delay Time	t _{d(on)}	V _{DD} = -6V, V _{GS} = -4.5V, R _L = 6Ω, R _G = 6Ω, I _D = -1A	-		17	ns
Turn-Off Delay Time	t _{d(off)}		-		35	ns

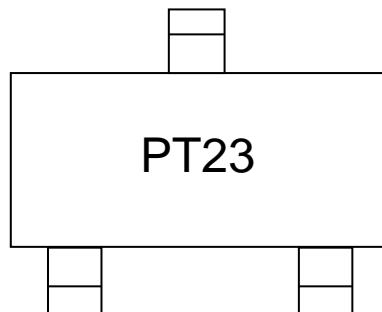
Absolute maximum rating@25°C

Rating		Symbol	Value	Units
Drain-Source Voltage		V _{DS}	-20	V
Gate-Source Voltage		V _{GS}	±8	V
Drain Current	Continuous	I _D	-2.8	A
	Pulsed	I _D	-8	A
Total Power Dissipation	T _A =25°C	P _D	900	mW
	T _A =125°C	P _D	570	mW
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 To 150	°C

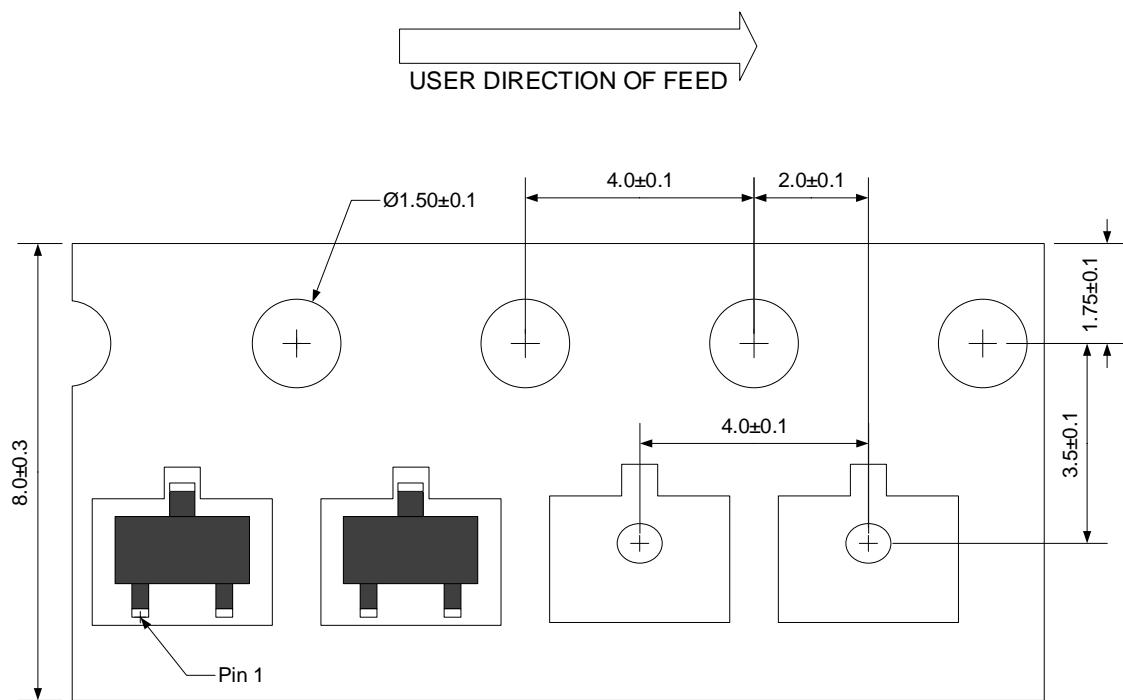
Typical Characteristics

Fig 1. Output Characteristics

Fig 2. Transfer Characteristics

Fig 3. On-Resistance vs. Drain Current

Fig 4. Capacitance

Product dimension(SOT-23)



Marking information**Ordering information**

Device	Package	Reel	Shipping
PPMT20V3	SOT-23 (Pb-Free)	7"	3000 / Tape & Reel

Load With Information

Unit:mm

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